162162
G00002

ETCH PROCESS FOR 3D FLASH STRUCTURES

ABSTRACT OF THE DISCLOSURE

A method for etching features in a plurality of silicon based bilayers forming a stack on a wafer in a plasma processing chamber is provided. A main etch gas is flowed into the plasma processing chamber. The main etch gas is formed into a plasma, while providing a first pressure. A wafer temperature of less than 20° C is maintained. The pressure is ramped to a second pressure less than the first pressure as the plasma etches through a plurality of the plurality of silicon based bilayers. The flow of the main etch gas is stopped after a first plurality of the plurality of bilayers is etched.

FIG. 1